## **Supporting Information**

## Wavelength-Tunable Green Light Sources Based on ZnO:Ga Nanowire/p-InGaN Heterojunctions

Maosheng Liu,<sup>†</sup> Mingming Jiang,<sup>\*,†</sup> Yang Liu,<sup>†</sup> Kai Tang,<sup>†</sup> Da Ning Shi<sup>†</sup> and Caixia

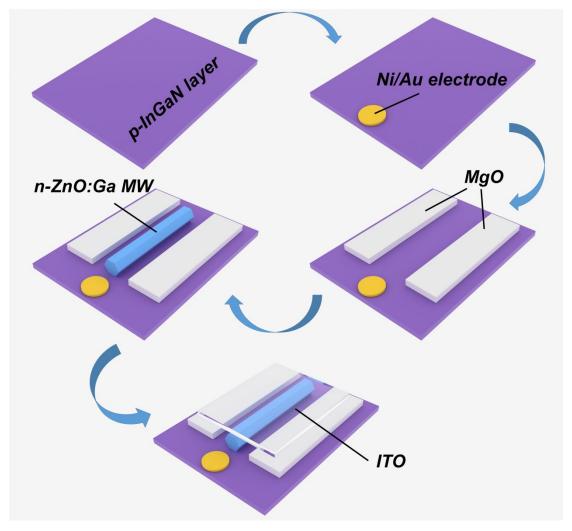
Kan<sup>\*,†</sup>

<sup>†</sup>College of Science, MIIT Key Laboratory of Aerospace Information Materials and Physics, Key Laboratory for Intelligent Nano Materials and Devices, Nanjing University of Aeronautics and Astronautics, No. 29 Jiangjun Road, Nanjing 211106, P. R. China.

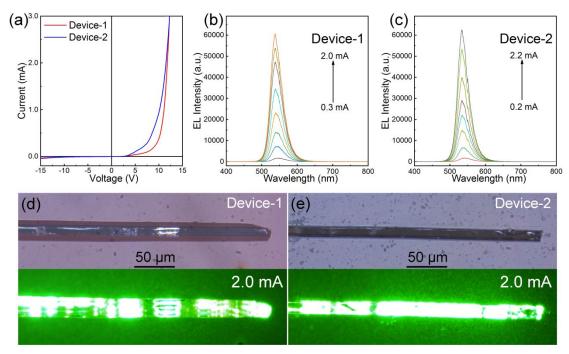
Corresponding author:

(Jiang M. M.) E-mail: mmjiang@nuaa.edu.cn.

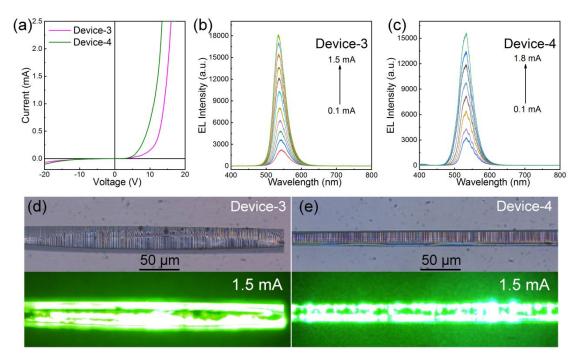
(Kan C. X.) E-mail: cxkan@nuaa.edu.cn.



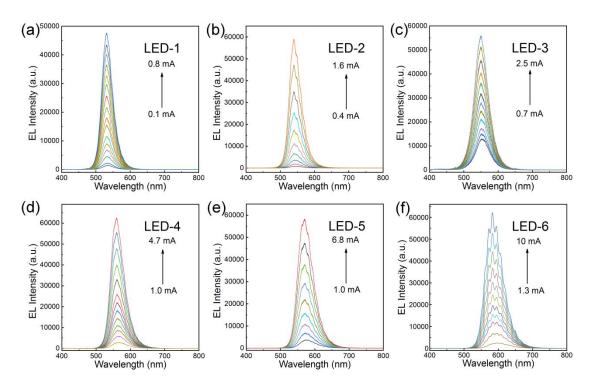
**Figure S1**. Brief preparation process of the n-ZnO:Ga MW/p-InGaN heterojunction LED.



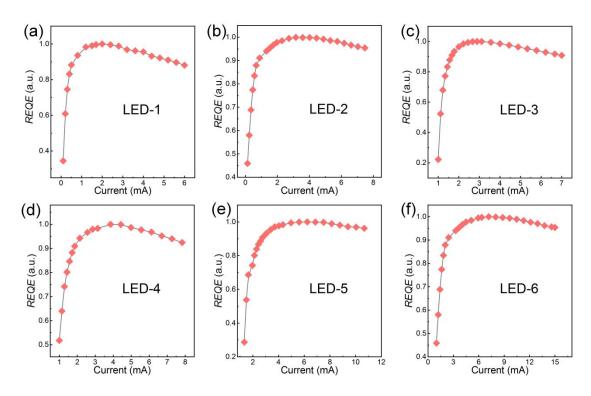
**Figure S2.** Device characterization of the as-constructed n-ZnO:Ga MW/p-InGaN heterojunction LEDs, with the MWs possessing hexagon-shaped cross section and different sizes. (a) I-V curves of Device-1 and Device-2, respectively. EL spectra of Device-1 (b), and Device-2 (c) under different injection current, respectively. Optical microscope EL images of Device-1 (d) and Device-2 (e), which being captured when the devices operated at an injection current of 2.0 mA.



**Figure S3.** Device characterization of the as-constructed n-ZnO:Ga MW/p-InGaN heterojunction LEDs, with the MWs possessing quadrilateral cross section and different sizes. (a) I-V curves of the fabricated Device-3 and Device-4, respectively. EL spectra of Device-3 (b), and Device-4 (c) under different injection current, respectively. Optical microscope EL images of Device-3 (d) and Device-4 (e), which being captured when the devices operated at an injection current of 1.5 mA.



**Figure S4.** EL spectra of as-fabricated one-dimensional wired n-ZnO:Ga/p-InGaN heterojunction LEDs by varying injection current. (a) for LED-1; (b) for LED-2; (c) for LED-3; (d) for LED-4; (e) for LED-5; (f) for LED-6.



**Figure S5.** The calculated *REQE* of as-fabricated one-dimensional wired n-ZnO:Ga/p-InGaN heterojunction LEDs. (a) for LED-1; (b) for LED-2; (c) for LED-3; (d) for LED-4; (e) for LED-5; (f) for LED-6.